



2N70K

Power MOSFET

2 Amps, 700 Volts N-CHANNEL POWER MOSFET

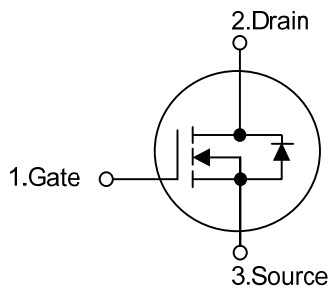
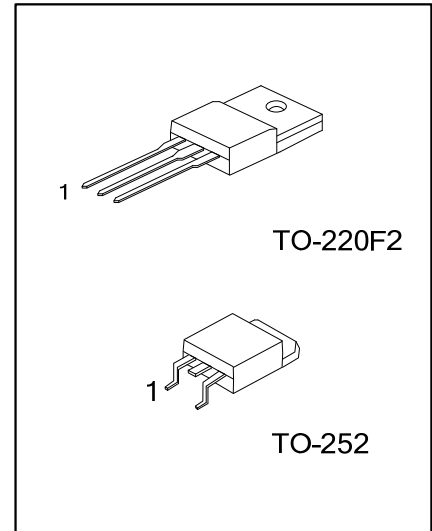
DESCRIPTION

The UTC **2N70K** is a high voltage MOSFET designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

- * $R_{DS(ON)} < 7.5\Omega @ V_{GS} = 10V$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL



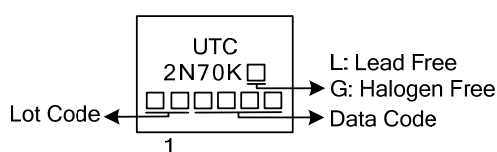
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2N70KL-TF2-T	2N70KG-TF2-T	TO-220F2	G	D	S	Tube
2N70KL-TN3-R	2N70KG-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

	(1)Packing Type	(1) T: Tube, R: Tape Reel
	(2)Package Type	(2) TF2: TO-220F2, TN3:TO-252
	(3)Lead Plating	(3) L: Lead Free, G: Halogen Free

MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	700	V
Gate-Source Voltage		V_{GSS}	± 30	V
Avalanche Current (Note 2)		I_{AR}	2.0	A
Drain Current	Continuous	I_D	2.0	A
	Pulsed (Note 2)	I_{DM}	8.0	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	20	mJ
	Repetitive (Note 2)	E_{AR}	2.8	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation	TO-220F2	P_D	40	W
	TO-252		30	
Junction Temperature		T_J	+150	$^\circ\text{C}$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by T_J .

3. $L=10\text{mH}$, $I_{AS}=2.0\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 2.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F2	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-252		110	
Junction to Case	TO-220F2	θ_{JC}	3.13	$^\circ\text{C/W}$
	TO-252		4.24	

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	$V_{GS} = 0V, I_D = 250\mu A$	700			V
Drain-Source Leakage Current		I_{DSS}	$V_{DS} = 700V, V_{GS} = 0V$			10	μA
Gate-Source Leakage Current	Forward	I_{GSS}	$V_{GS} = 30V, V_{DS} = 0V$			100	nA
	Reverse		$V_{GS} = -30V, V_{DS} = 0V$			-100	nA
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS} / \Delta T_J$	$I_D = 250\mu A$, Referenced to 25°C		0.4		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0		4.0	V
Static Drain-Source On-State Resistance		$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 1A$		6.8	7.5	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C_{ISS}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$		270	350	pF
Output Capacitance		C_{OSS}			38	50	pF
Reverse Transfer Capacitance		C_{RSS}			5	7	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		$t_{D(ON)}$	$V_{DD} = 30V, I_D = 0.5A, R_G = 25\Omega$ (Note 1, 2)		28	50	ns
Turn-On Rise Time		t_R			40	45	ns
Turn-Off Delay Time		$t_{D(OFF)}$			50	60	ns
Turn-Off Fall Time		t_F			25	30	ns
Total Gate Charge		Q_G	$V_{DS} = 50V, V_{GS} = 10V, I_D = 1.3A$ $I_G = 100\mu A$ (Note 1, 2)		19	30	nC
Gate-Source Charge		Q_{GS}			7		nC
Gate-Drain Charge		Q_{GD}			2.1		nC
DRAIN-SOURCE DIODE CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V_{SD}	$V_{GS} = 0V, I_{SD} = 2.0A$			1.4	V
Continuous Drain-Source Current		I_{SD}				2.0	A
Pulsed Drain-Source Current		I_{SM}				8.0	A

Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
 2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

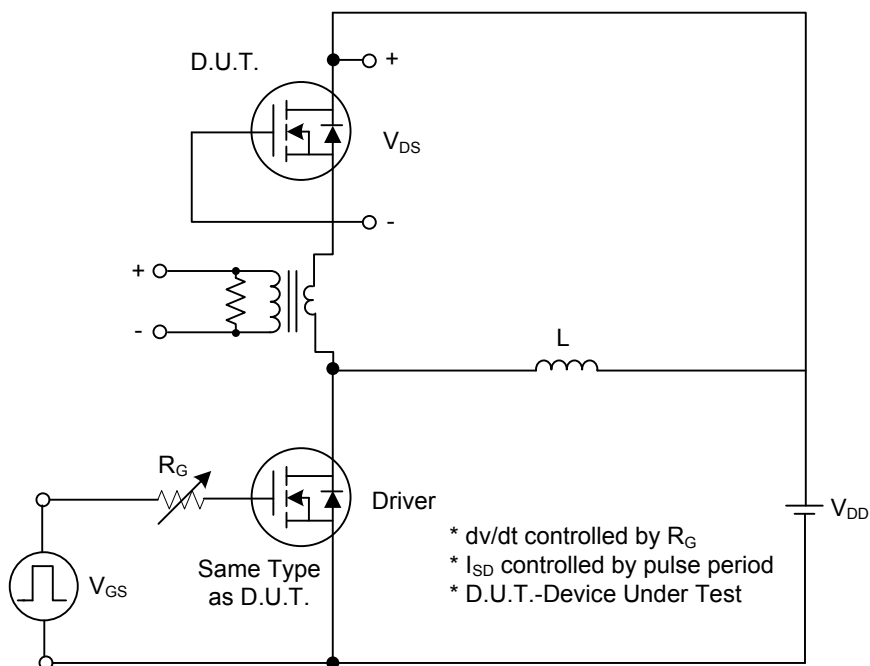


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

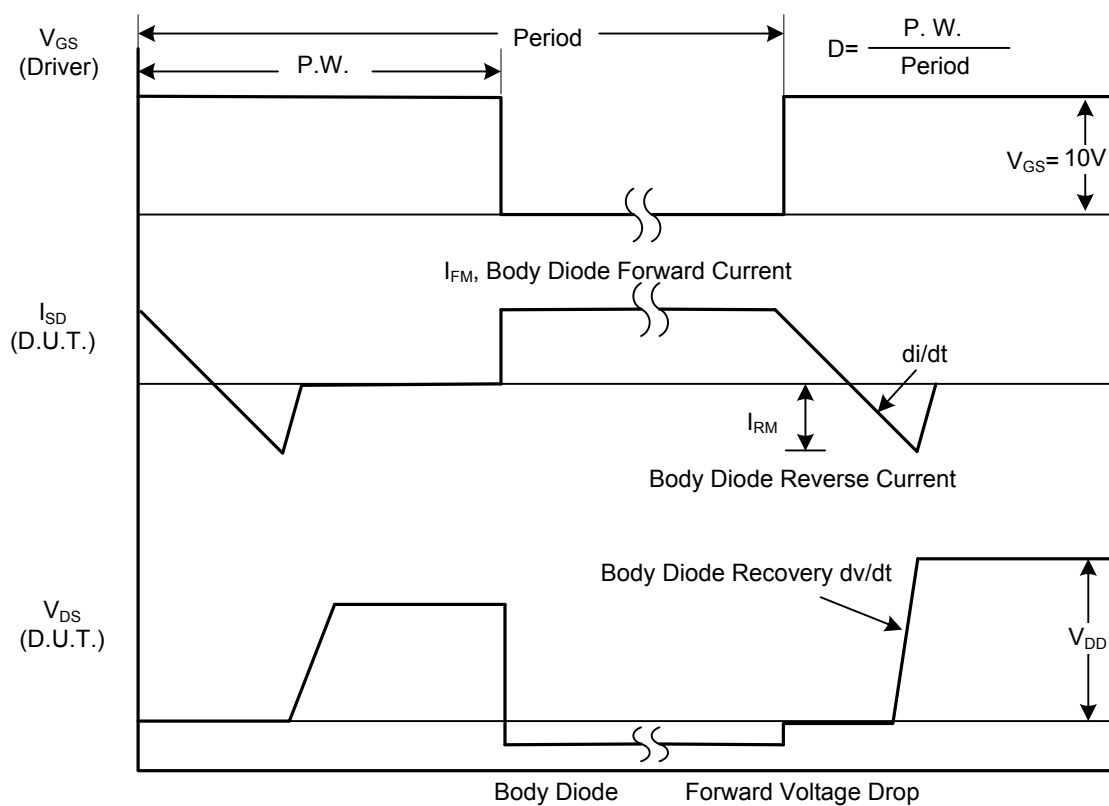


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

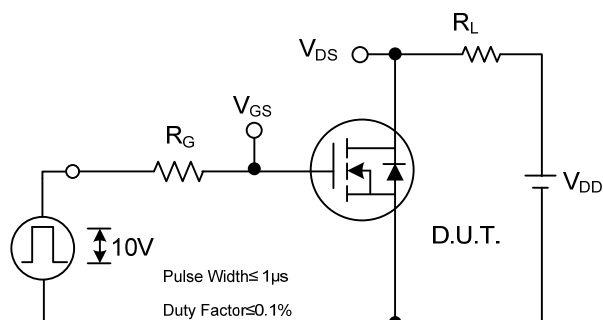


Fig. 2A Switching Test Circuit

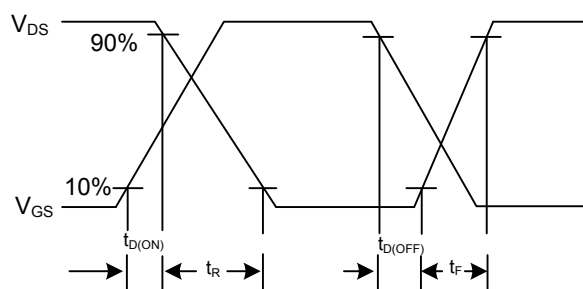


Fig. 2B Switching Waveforms

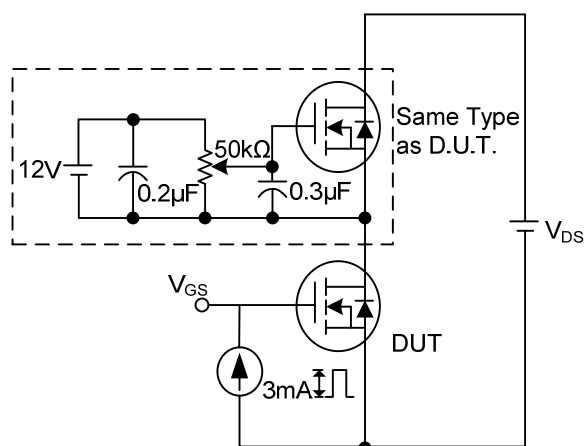


Fig. 3A Gate Charge Test Circuit

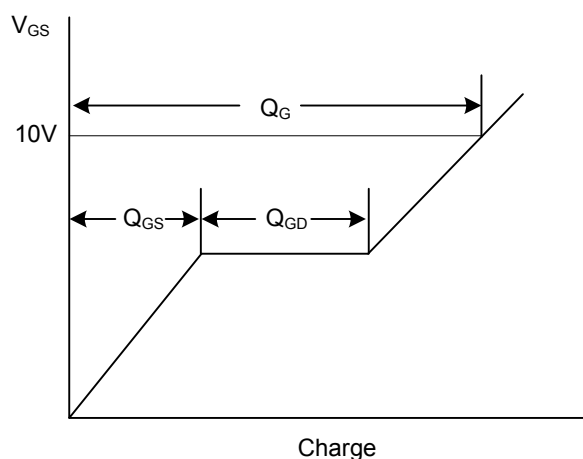


Fig. 3B Gate Charge Waveform

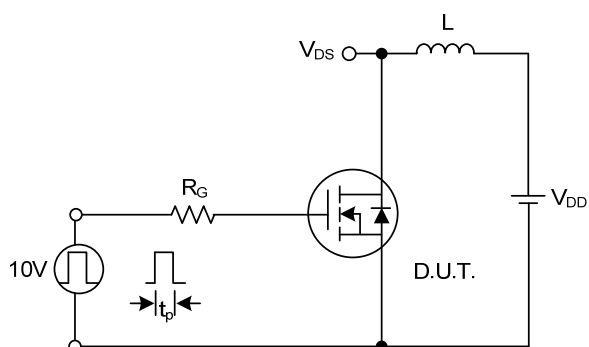


Fig. 4A Unclamped Inductive Switching Test Circuit

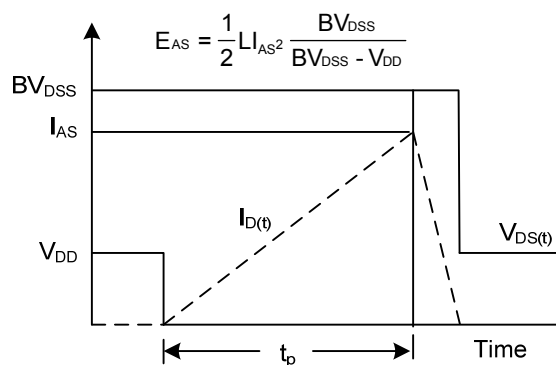
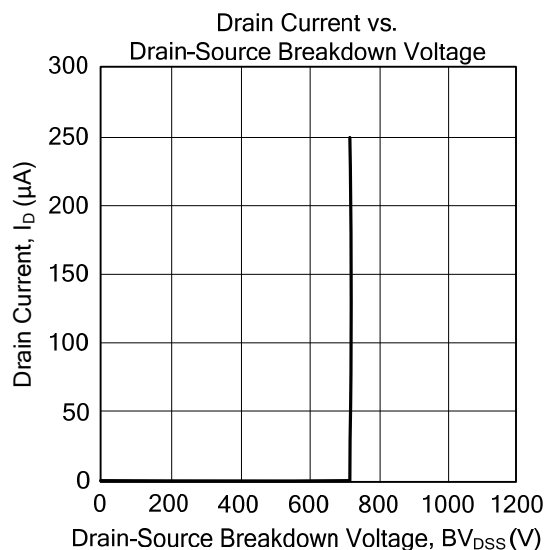
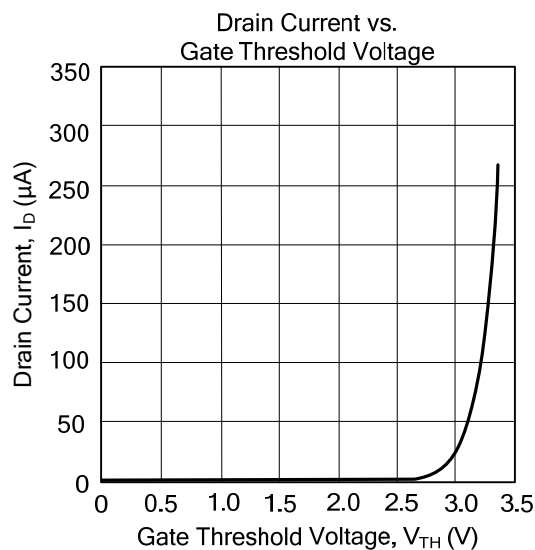
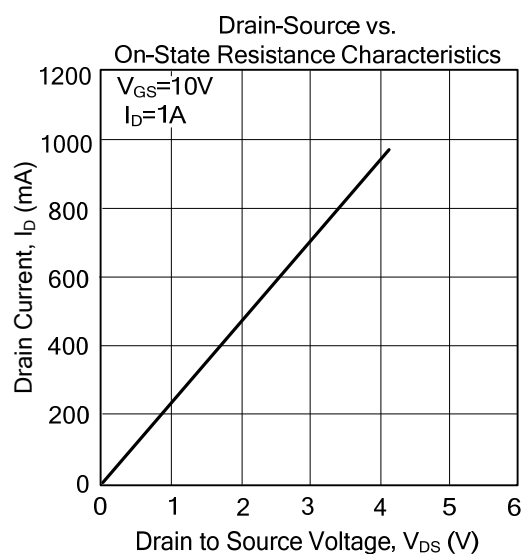
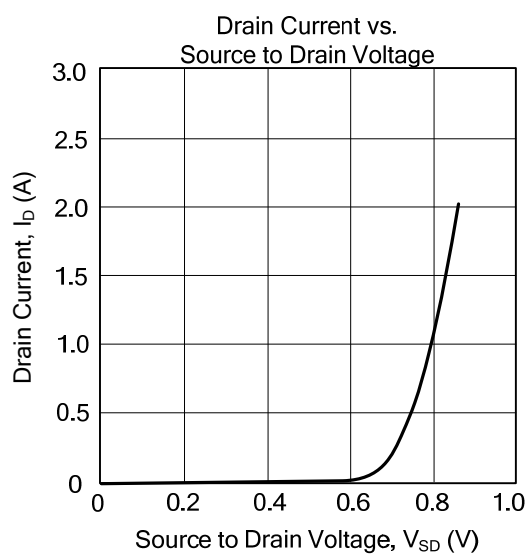


Fig. 4B Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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